

100V N-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

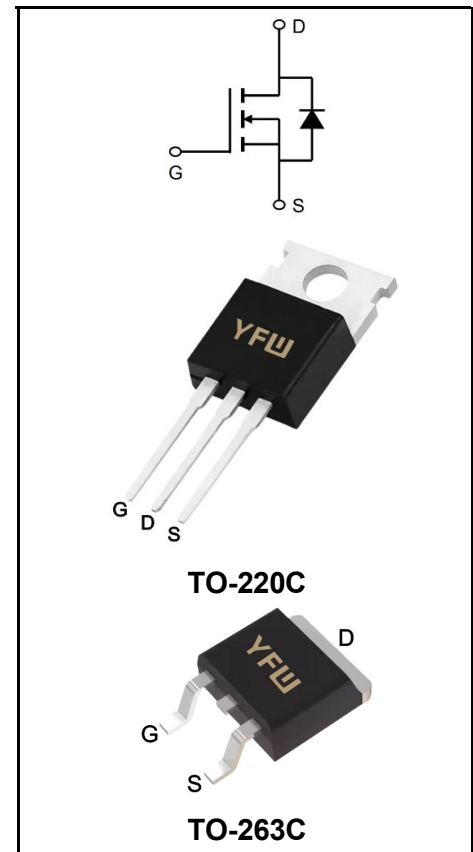
I_D	120A
V_{DSS}	100V
R_{DS(on)-typ}(@V_{GS}=10V)	<5.6mΩ (Type:4.5 mΩ)

APPLICATIONS

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply
- ◆ **YFW-SGT technology**

MECHANICAL DATA

- ◆ Case: Molded plastic
- ◆ Mounting Position: Any
- ◆ Molded Plastic: UL Flammability Classification Rating 94V-0
- ◆ Lead free in compliance with EU RoHS 2011/65/EU directive
- ◆ Solder bath temperature 275℃ maximum, 10s per JESD 22-B106



Maximum Ratings at Tc=25℃ unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	100	V
Gate - Source Voltage	V_{GS}	±20	V
Continue Drain Current	I_D	120	A
Pulsed Drain Current (Note1)	I_{DM}	520	A
Single Pulse Avalanche Energy (Note1)	E_{AS}	750	mJ
Total Power Dissipation	P_D	210	W
Storage Temperature Range	T_{STG}	-55 to +175	℃
Operating Junction Temperature Range	T_J	175	℃
Thermal Resistance, Junction to Ambient	R_{θJA}	55	℃/W
Thermal Resistance, Junction to Case	R_{θJC}	0.71	℃/W

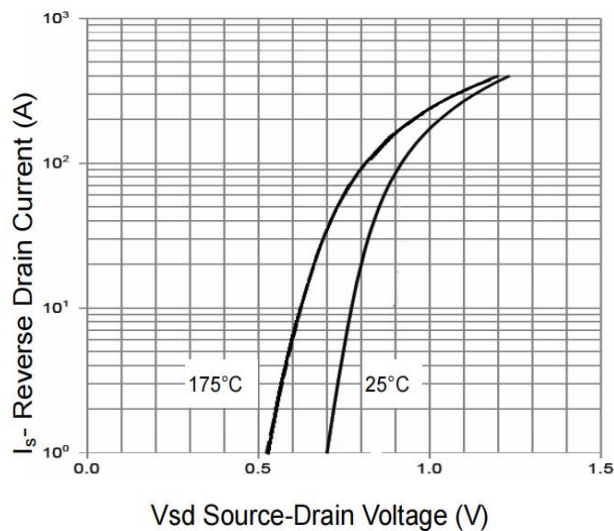
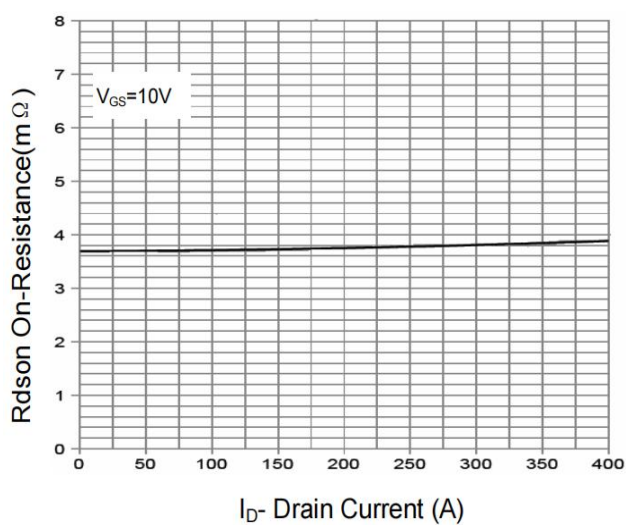
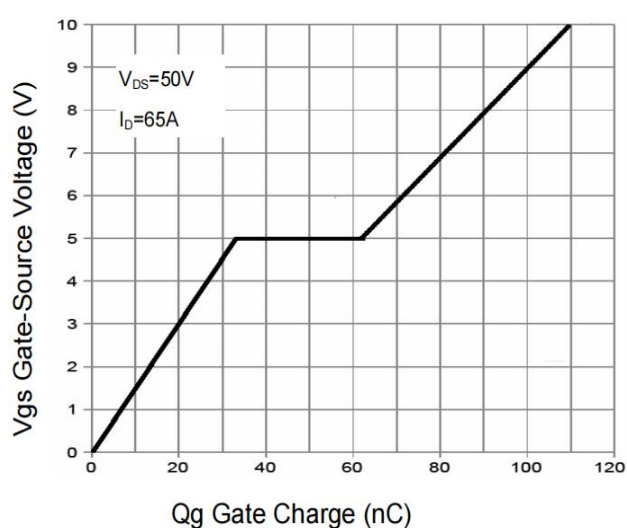
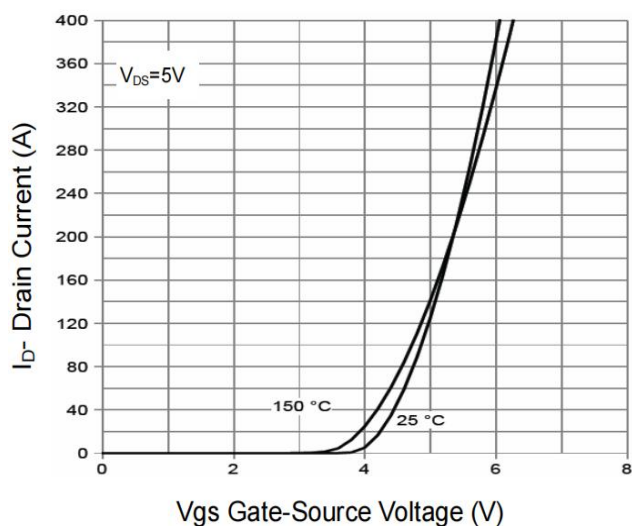
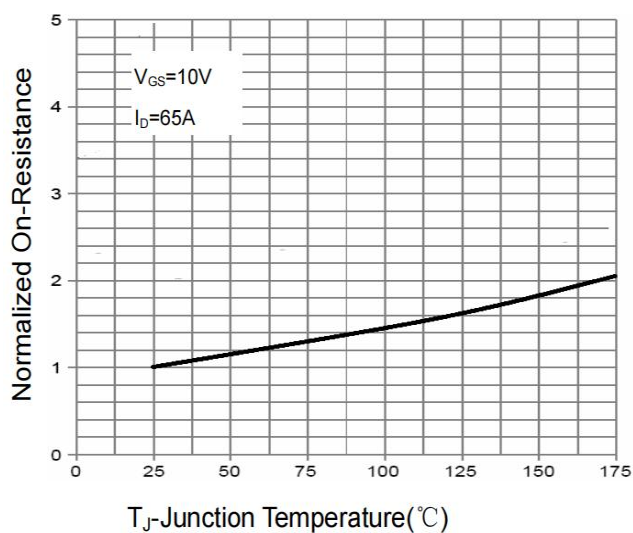
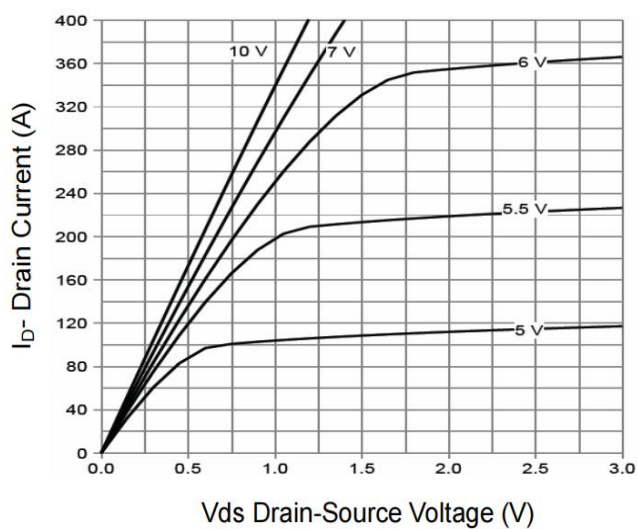
Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Maximum Ratings at Tc=25°C unless otherwise specified

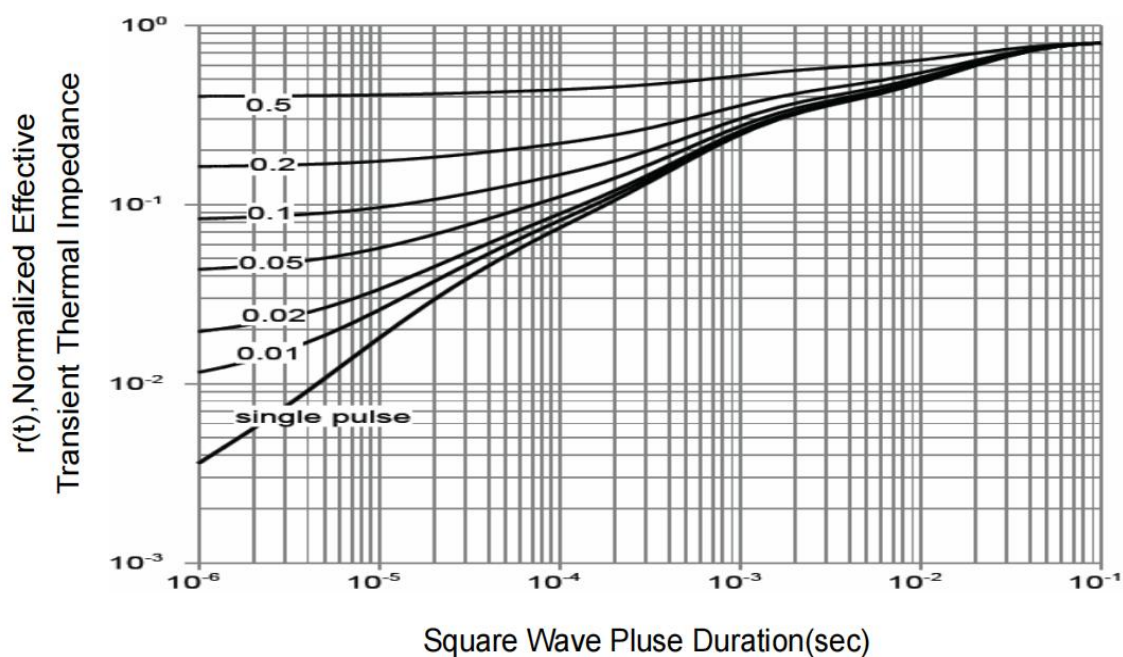
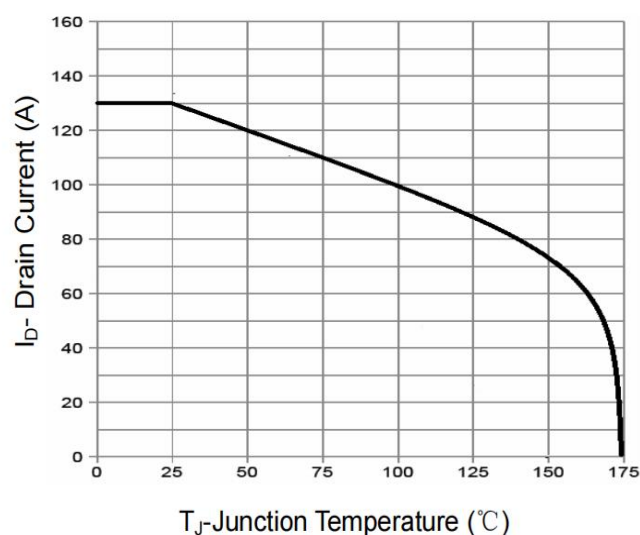
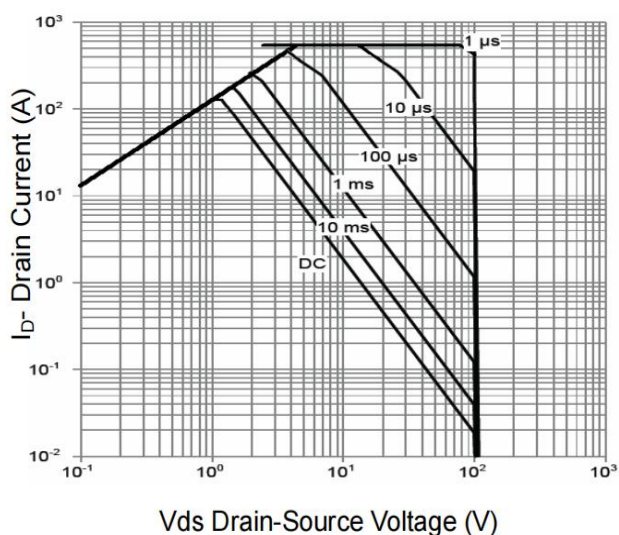
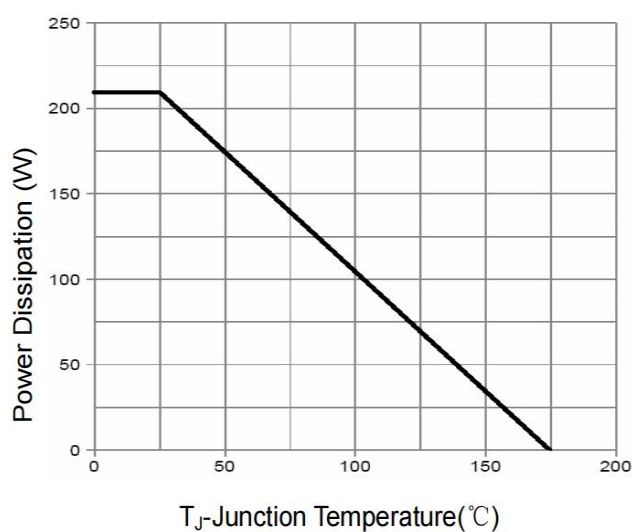
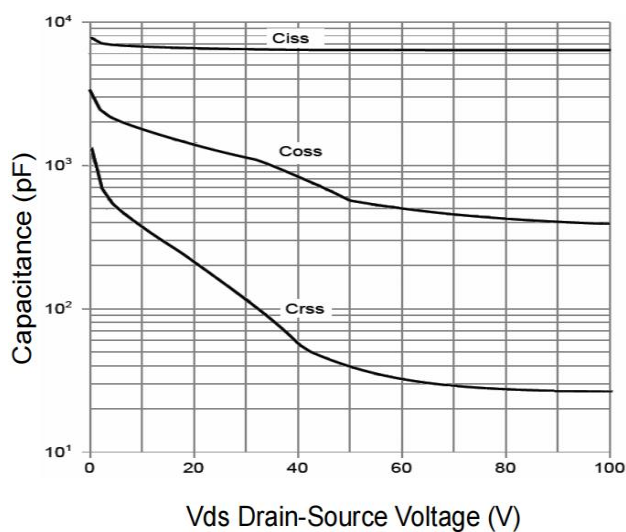
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	100	-	-	V
Gate Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	± 100	nA
Drain-Source Leakage Current	$V_{DS} = 100 V, V_{GS} = 0 V$	I_{DSS}	-	-	1	μA
Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	2.0	-	4.0	V
Drain-Source on-Resistance 4	$V_{GS}=10V, I_D=20A$	$R_{DS(ON)}$	-	4.5	5.6	m Ω
Forward Transconductance4	$V_{DS}=5V, I_D=65A$	g_{fs}	-	130	-	S
Input Capacitance	$V_{DS}=50V$ $V_{GS}=0V$ $f=1MHz$	C_{iss}	-	4350	-	μF
Output Capacitance		C_{oss}	-	2150	-	
Reverse Transfer Capacitance		C_{rss}	-	220	-	
Total Gate Charge	$V_{GS}=10V$ $V_{DS}=50V$ $I_D=65A$	Q_g	-	110	-	nC
Gate-Source Charge		Q_{gs}	-	33	-	
Gate-Drain Charge		Q_{gd}	-	30	-	
Turn-on delay time	$V_{GS}=10V$ $V_{DD}=50V$ $R_G=3\Omega$ $I_D=65A$	$t_{d(on)}$	-	23	-	ns
Rise Time		T_r	-	15	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	48	-	
Fall Time		t_f	-	16	-	
Body Diode Reverse Recovery Time(Note2)	$T_J = 25^\circ C, I_F = 65A$ $di / dt = 100 A/\mu s$	t_{rr}	-	70	-	ns
Body Diode Reverse Recovery Charge(Note2)		Q_{rr}	-	117	-	nC
Diode Forward Voltage	$V_{GS}=0V, I_S=40A, T_J=25^\circ C$	V_{SD}	-	0.86	1.2	V
Continuous Source Current		I_S	-	-	120	A

Note2:Pulse test: 300 μs pulse width, 2 % duty cycle

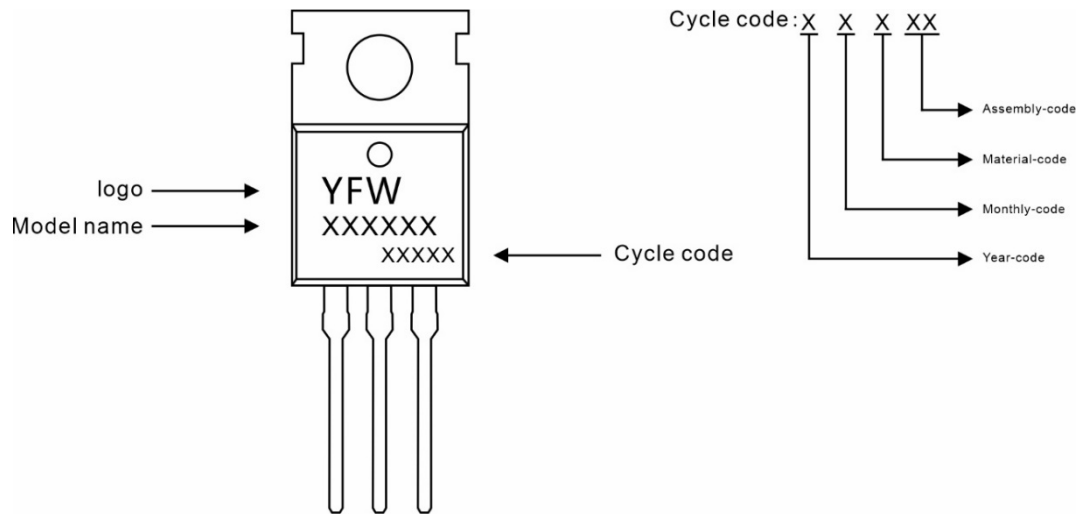
Ratings and Characteristic Curves



Ratings and Characteristic Curves



Marking Diagram



Ordering information

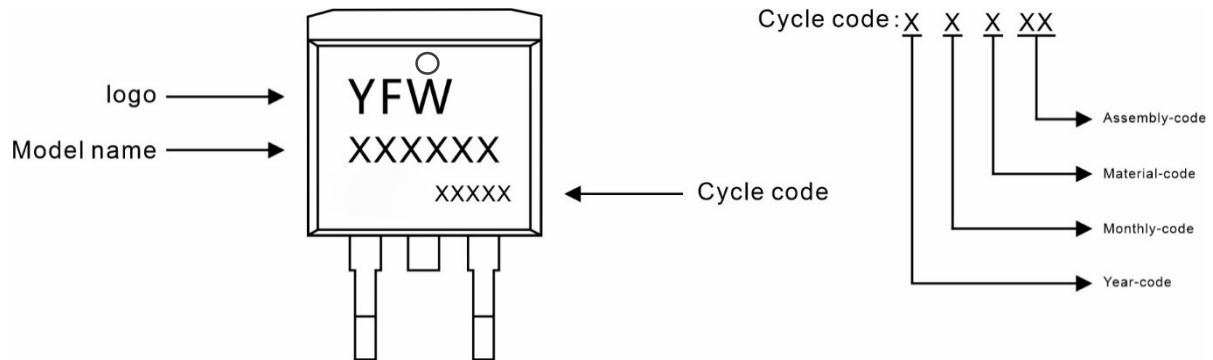
Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWG120N10AC	TO-220C	0.07oz(1.96g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

Package Dimensions

TO-220C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.34	4.67	0.171	0.184
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156

Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWG120N10ASC	TO-263C	0.04oz(1.16g)	800pcs/reel	1600pcs/box 8000pcs/Carton

Package Dimensions

TO-263C

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A1	0.00	0.15	0.000	0.006
A2	4.30	4.55	0.169	0.179
B	1.10	1.50	0.043	0.059
b	0.70	0.90	0.028	0.035
b1	1.20	1.50	0.047	0.059
c	0.30	0.60	0.012	0.024
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
L	15.00	15.30	0.591	0.602
L1	5.20	5.40	0.205	0.213
L2	2.40	2.60	0.094	0.102
L3	1.60	1.80	0.063	0.071

Disclaimer

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